

1SS110

Silicon Epitaxial Planar Diode for Tuner Band Switch

HITACHI

 Rev. 1
 Nov. 1994

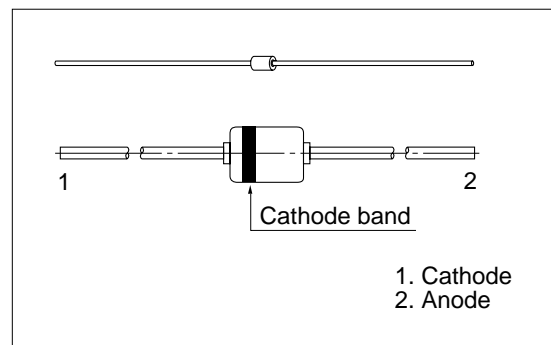
Features

- Low forward resistance. ($r_f = 0.9\Omega$ max)
- Suitable for 5mm pitch high speed automatic insertion.
- Small glass package (MHD) enables easy mounting and high reliability.

Ordering Information

Type No.	Cathode band	Package Code
1SS110	Verdure	MHD

Outline



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Value	Unit
Reverse voltage	V_R	35	V
Forward current	I_F	100	mA
Power dissipation	P_d	15.0	mW
Operation temperature	T_{opr}	-20 to + 60	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.0	V	$I_F = 10$ mA
Reverse voltage	V_R	35	—	—	V	$I_R = 10$ μA
Reverse current	I_R	—	—	0.1	μA	$V_R = 25$ V
Capacitance	C	—	—	1.2	pF	$V_R = 6$ V , $f = 1$ MHz
Forward resistance	r_f	—	—	0.9	Ω	$I_F = 2$ mA , $f = 100$ MHz

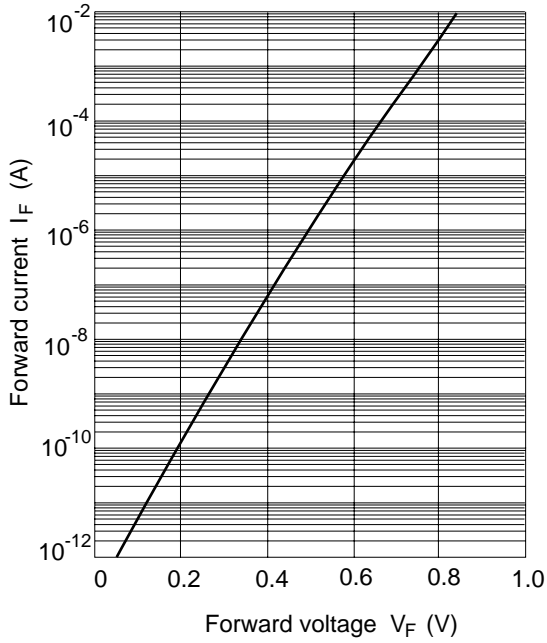


Fig.1 Forward current Vs. Forward voltage

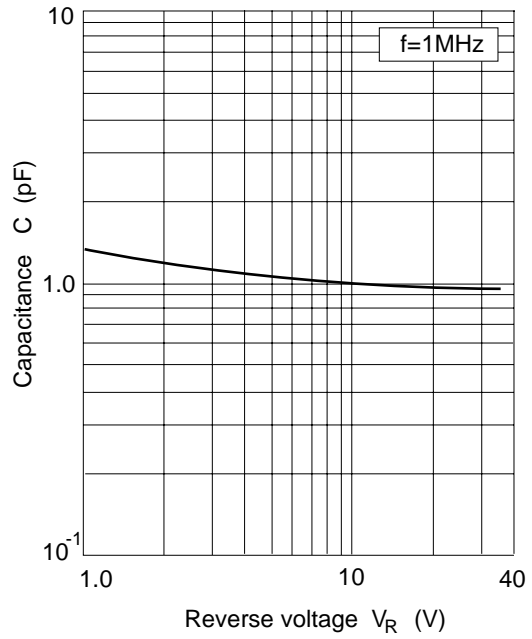


Fig.2 Capacitance Vs. Reverse voltage

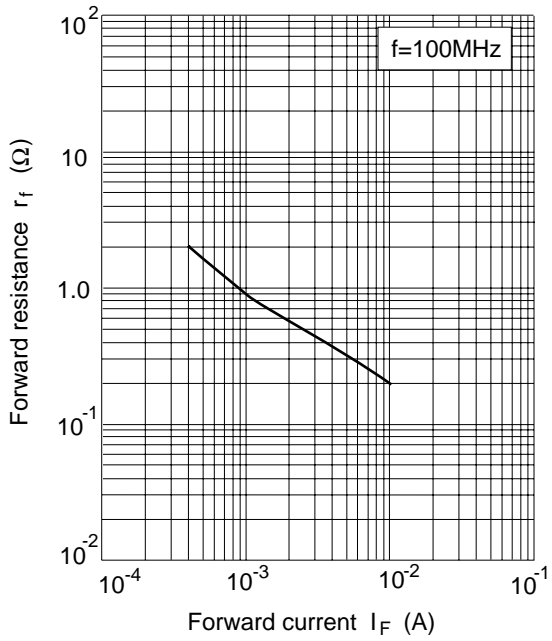
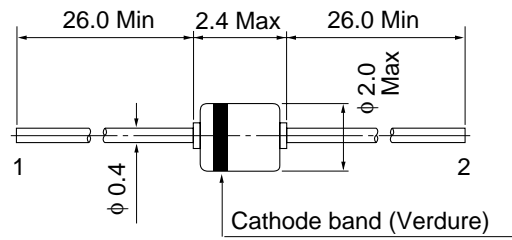


Fig.3 Forward resistance Vs. Forward current

Package Dimensions

Unit: mm



- 1 Cathode
- 2 Anode

HITACHI Code	MHD
JEDEC Code	DO-34
EIAJ Code	—
Weight (g)	0.084